

*Morphology and High-temperature
Stability of Thin Alumina Coatings
Deposited on Si, SiC, and Ni*

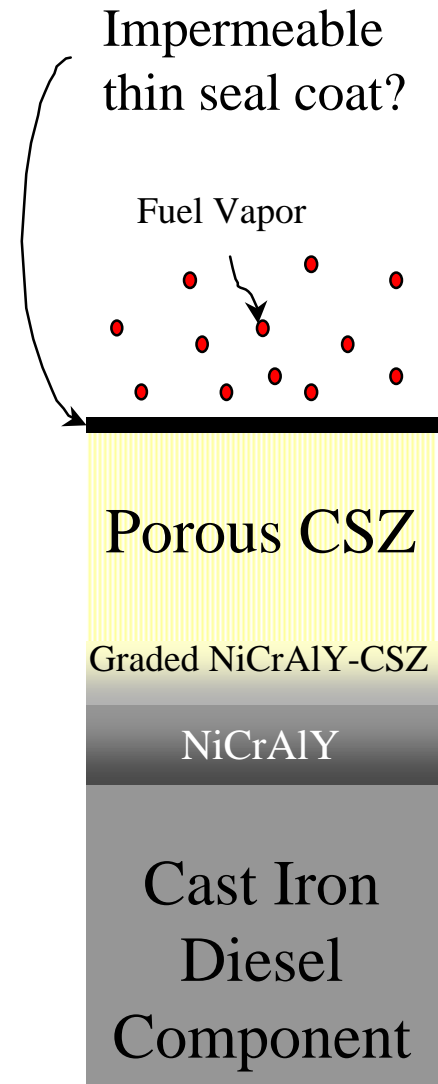
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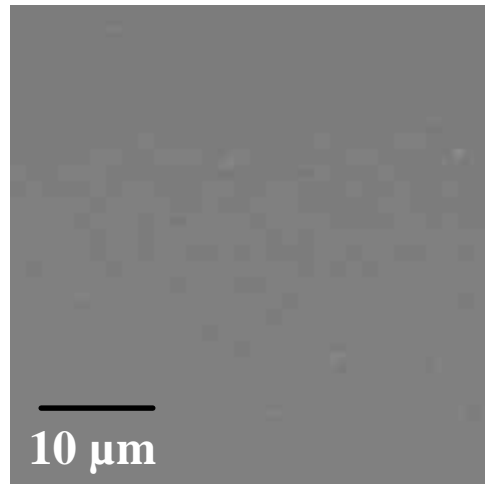
January 14, 1999

Initial Seal Coating Work Reveals Volume Shrinkage Due to Crystallization: A Serious Obstacle

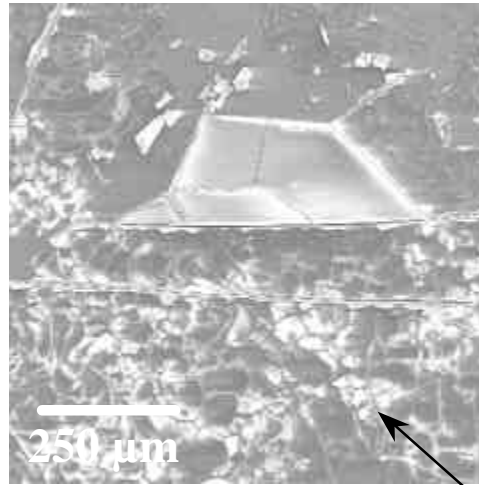
- Thermal Barrier Coatings (TBCs) are being considered to improve diesel engine efficiency
 - CeO_2 -stabilized ZrO_2 (CSZ) prepared by air plasma spray (APS) is made porous for strain tolerance and enhanced thermal insulation
- Unexpectedly, testing at Caterpillar revealed a decrease in engine efficiency when components were coated with a TBC
 - One possible reason may be the porosity of the TBC, which is suspected to “entrain” fuel from the combustion chamber prior to ignition [B. Beardsley, 1990]
- Thick MOCVD Al_2O_3 coatings deposited on APS-CSZ adhered, but cracked significantly



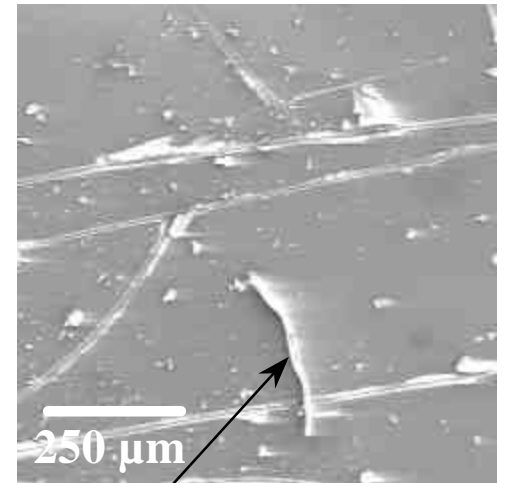
Thick (2.25 μm) Al_2O_3 on Si Spalled upon Annealing



As coated

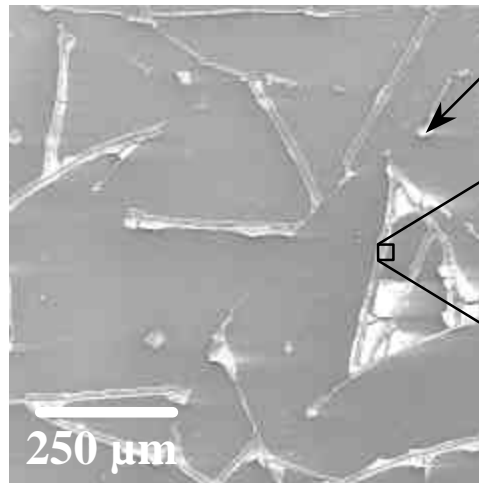
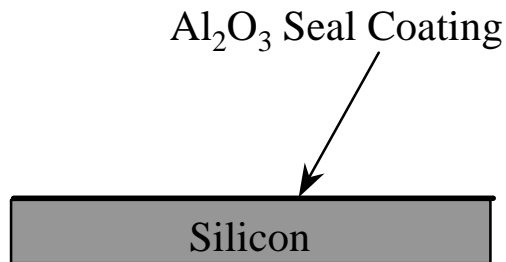


800°C



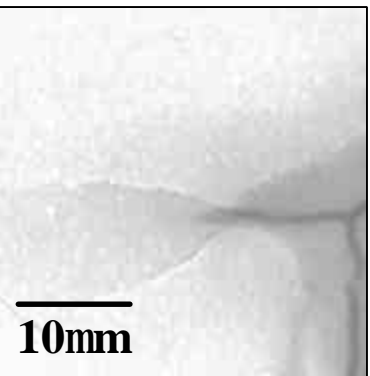
900°C

Non-spalled Al_2O_3



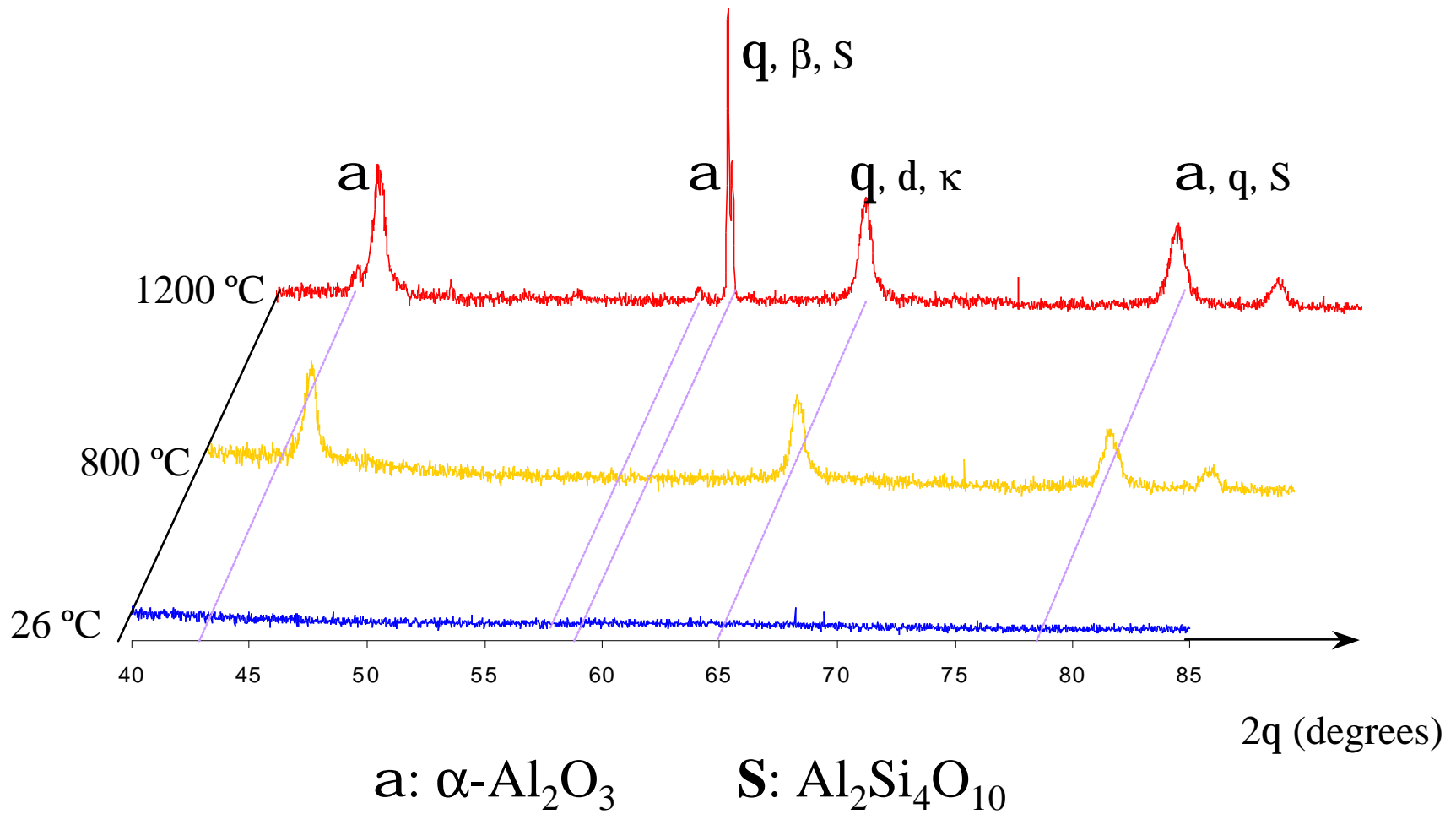
1200°C

200x



10 μm

Crystallization of Al_2O_3 Occurs Relatively Rapidly (< 20 Hours) at 700°C to 1200°C



Not much Al_2O_3 remained on the substrate for XRD analysis

Spalling of Al₂O₃ Seal Coatings May Be Avoided by Reducing Coating Thickness

- Annealing of thick (2.25 μm) MOCVD Al₂O₃ coatings leads to inadequate adhesion and sealing
 - Considerable spallation on silicon due to:
 - CTE mismatch
 - Volume shrinkage due to crystallization
 - Adhered on CSZ, but coating cracked as crystallization occurred
 - Less CTE mismatch with CSZ than with Si
 - Better adhesion may be due to mechanical interlocking at CSZ/coating interface
 - Volume shrinkage still significant (~ 9%)
- Work by F.F. Lange stipulates that thin coatings (~100nm) are better able to contain tensile stress systems
 - crack propagation occurs only when free energy of any film would be reduced; strain energy depends on film thickness
 - There is a critical film thickness associated with a maximum internal energy

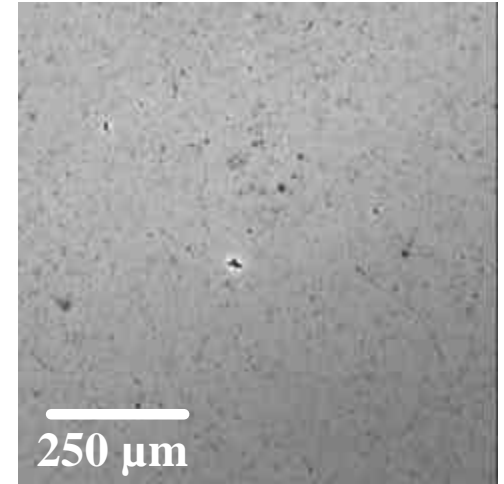
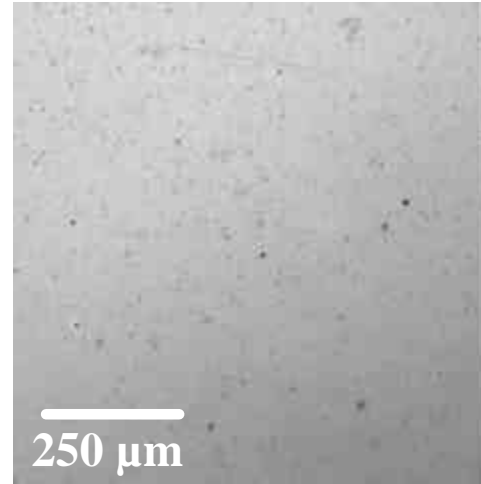
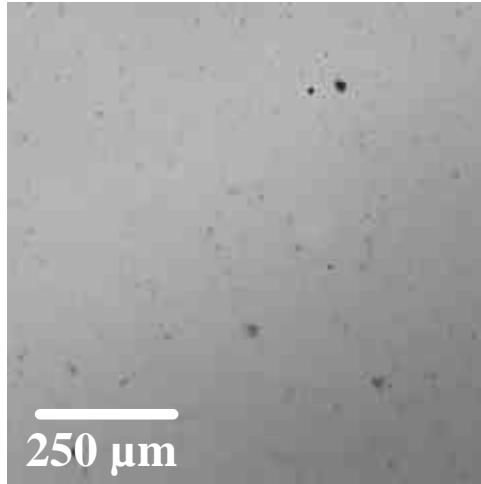
Sub-micron Coatings Exhibited Slight Cracking

290 nm

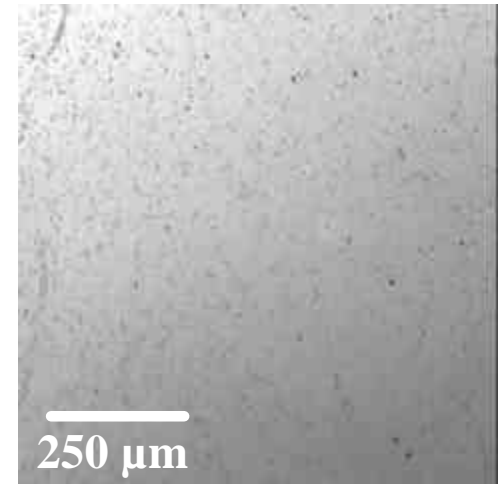
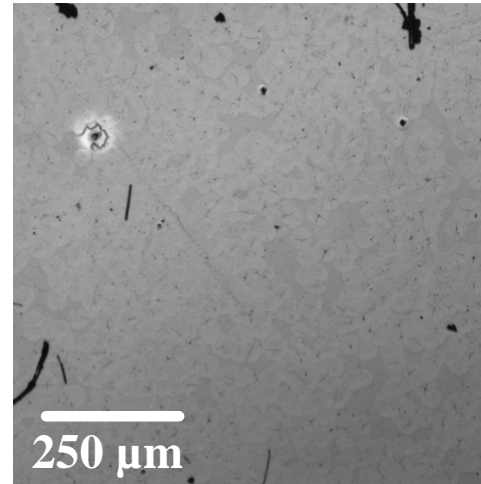
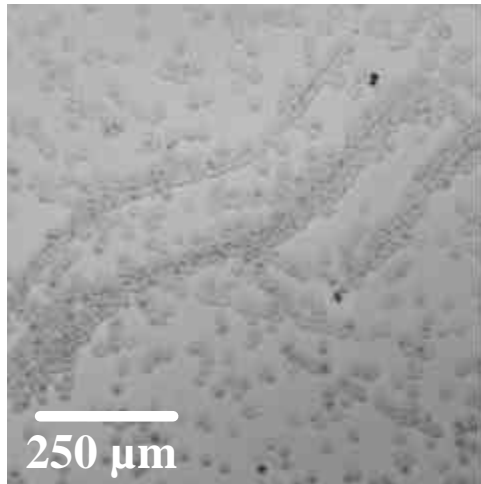
260 nm

160 nm

700°C



1100°C



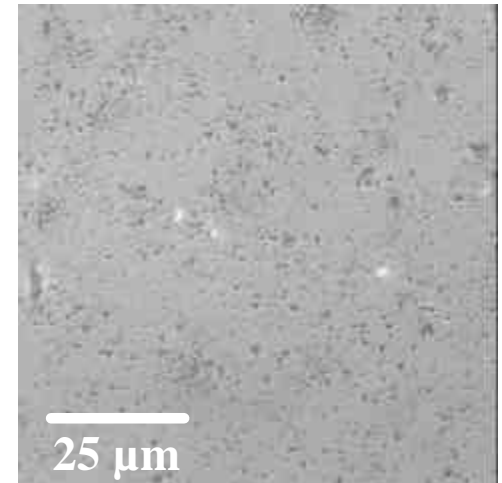
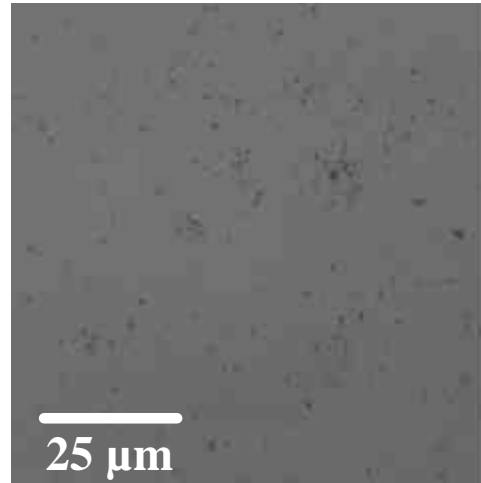
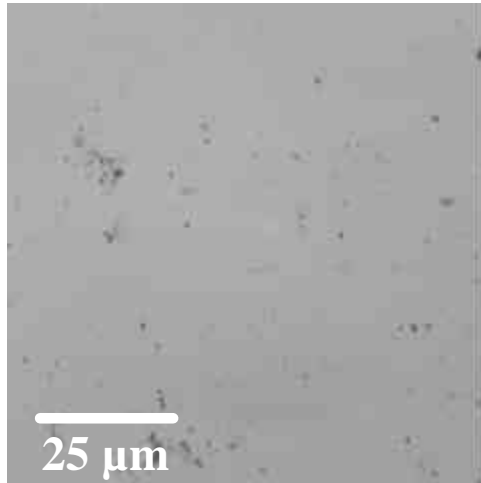
Micro-Cracking Falls With Coating Thickness

290 nm

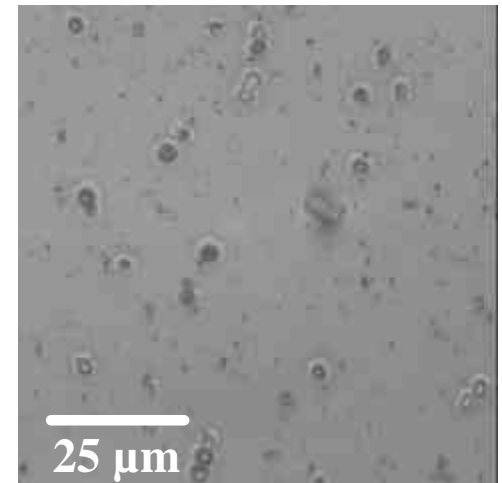
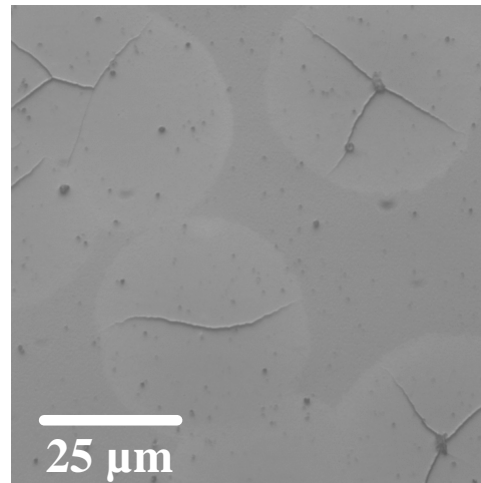
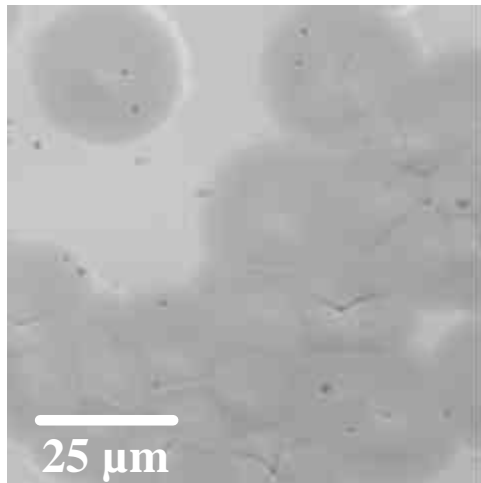
260 nm

160 nm

700°C



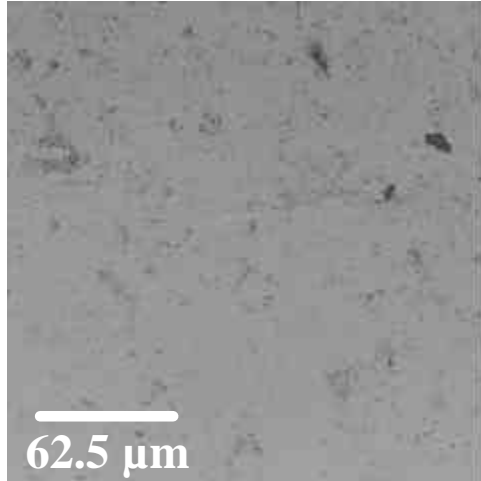
1100°C



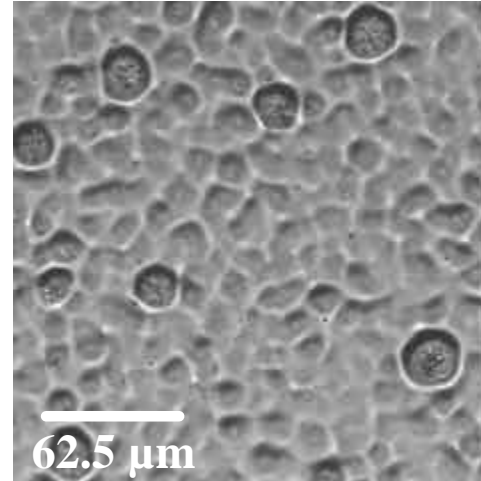
Silicon Carbide & Nickel Alloy Substrates at 1100°C

770 nm (26°C)

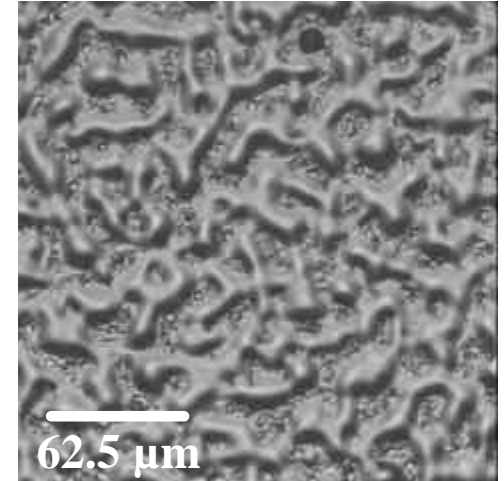
SiC



830 nm

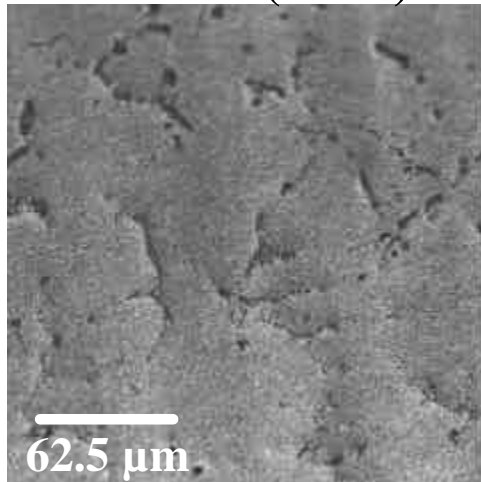


510 nm

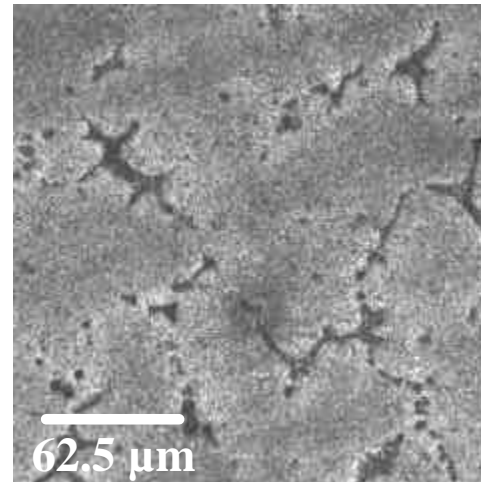


760 nm (26°C)

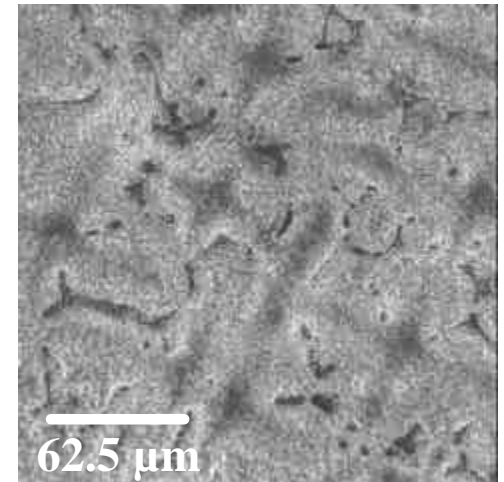
Ni alloy



960 nm

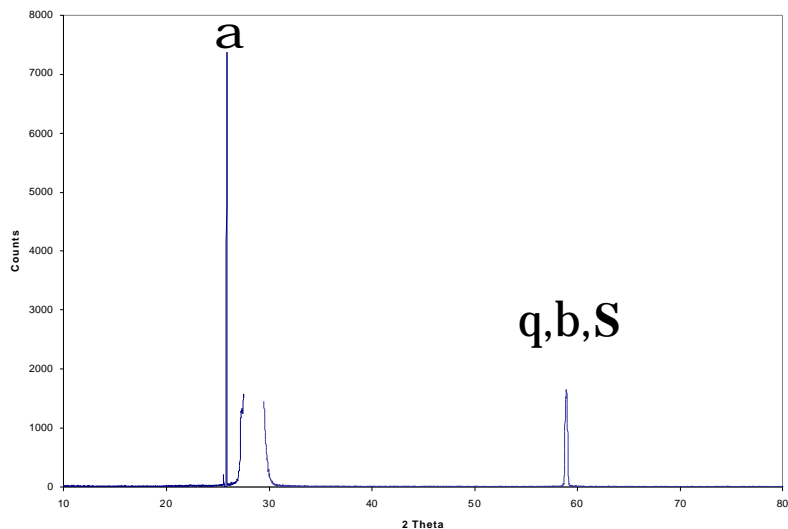


540 nm

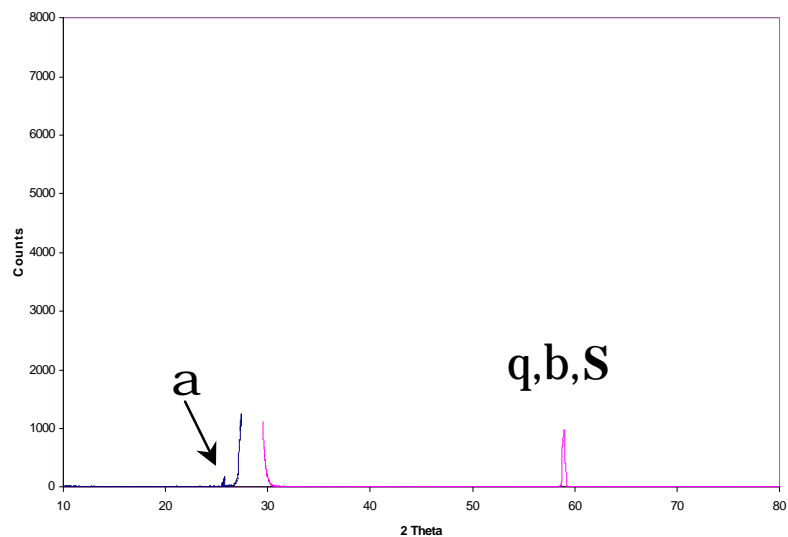


XRD Demonstrates Only Minimal Transformation

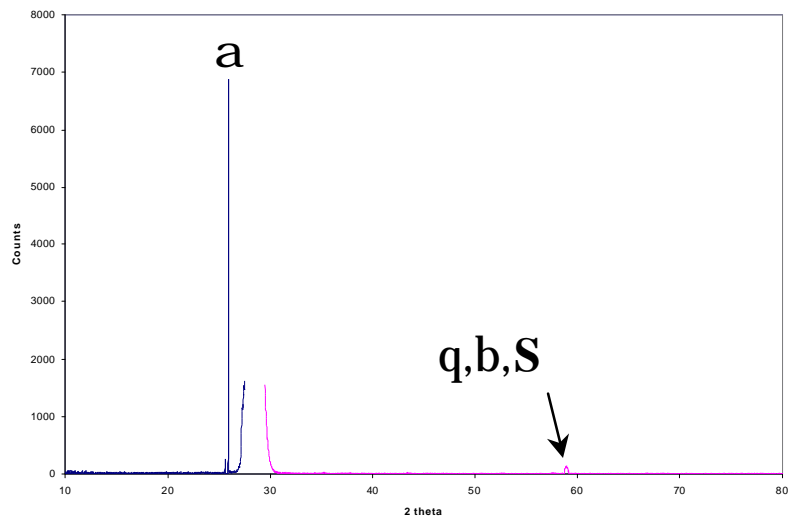
Alumina on Si (35-AO-02)



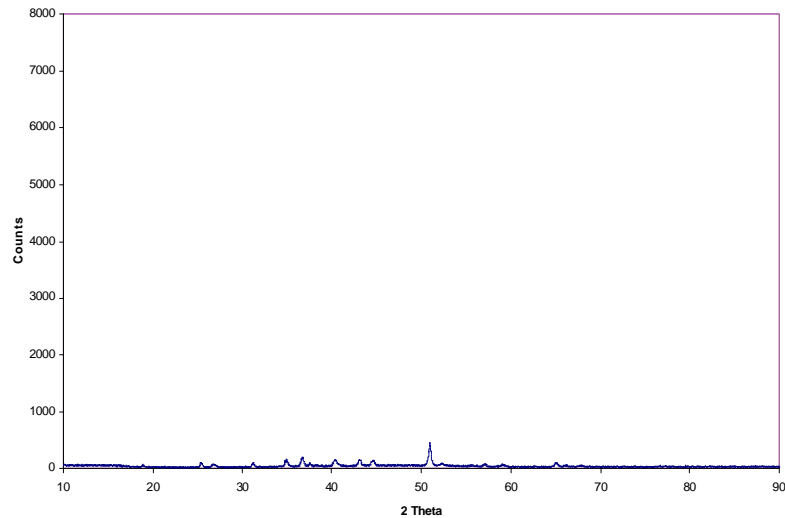
Alumina on Si, Annealed at 700C (36-AO-01)



Alumina on Si, Annealed at 1100C (37-AO-01)



Alumina on Ni, Annealed at 1100C (39-AO-02)

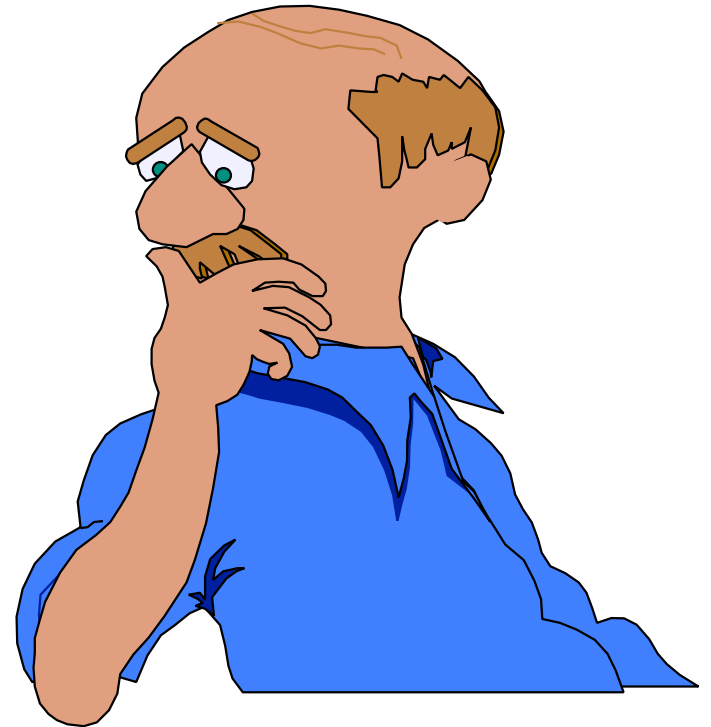


Annealing of Al₂O₃ Coatings at 1100°C for 20 Hours Showed Several Thickness-based Trends

- Thinner coatings on silicon appear to maintain a lower distribution of crack-initiating “pores”
- Despite this, transformation is not evident in XRD patterns, requiring additional effort to confirm Al₂O₃ crystallization
- Coatings on silicon carbide appear to “coagulate” more easily as thickness drops, especially in center of samples
- Coatings on nickel alloy substrates demonstrate increased leveling as thickness decreases
- With confirmation of crystallinity, sub-100nm coatings can be analyzed for micro-cracks

Substrate Heating Issues Considered

- Atmospheric plasma processing
 - High energy, very low substrate temperature
 - High reaction area/volume inherent to process
- Flat, resistive element heater
 - Increased substrate temperature, expensive
 - Low maximum temperature
- Optical heating methods
 - esoteric and complex



Non-equilibrium, Atmospheric Plasma Processing

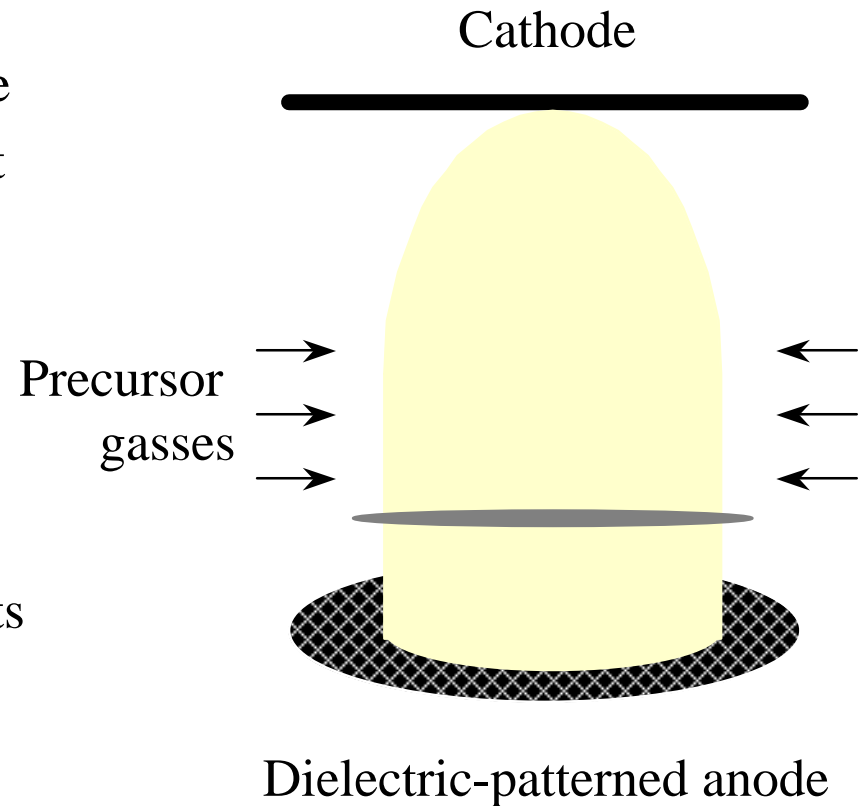
(Luis Amorer & Prof. Kunhardt)

- Advantages

- Processing at atmospheric pressure
- Minimal substrate heating (can put hand in plasma)
- High $T_e \sim 0.2 - 0.3 \text{ keV} \gg T_i \sim T_n$
- Large processing area/volume

- Obstacles

- Plasma only just beginning to be characterized (no conclusive results of any nature, yet)
- Anodes are fabricated using by depositing a highly-complex pattern of a high-dielectric material on the base anode material



Flat High-temperature Resistive Heater May Be too Expensive

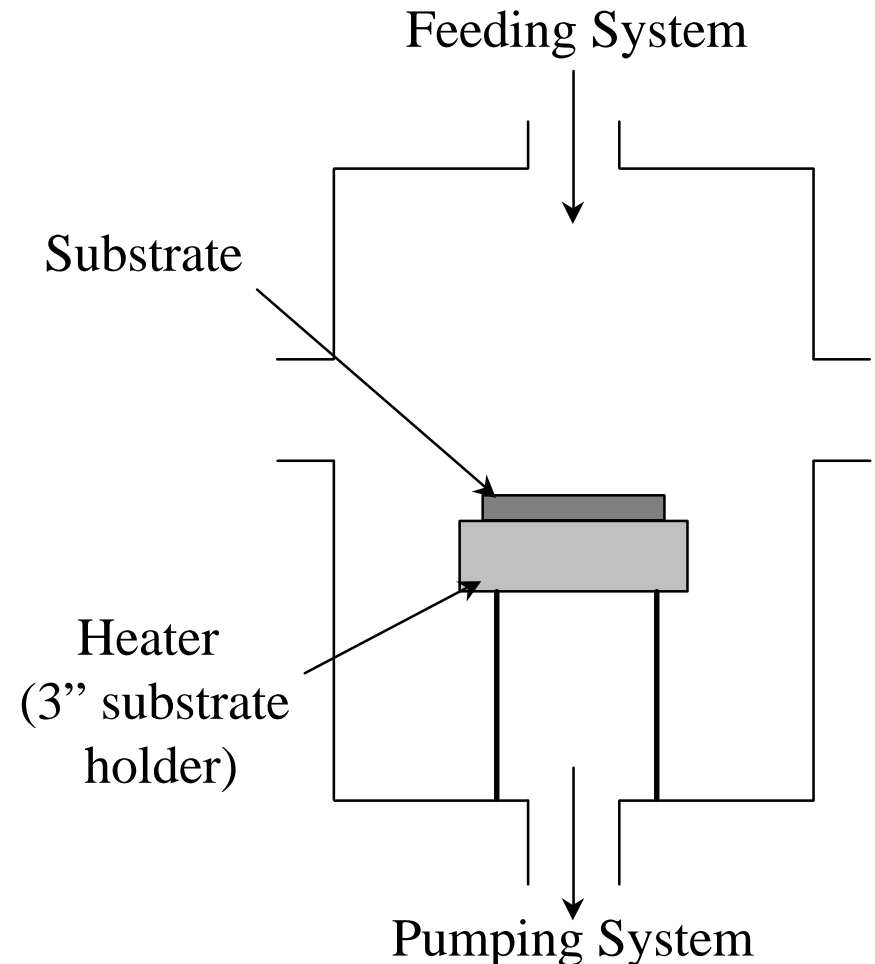
(Bell Labs / US, Inc. Thin Film Products)

- Advantages

- Excellent temperature stability ($\pm 2^{\circ}\text{C}$) and uniformity ($\pm 8^{\circ}\text{C}$)
- Short ramp time of 20 minutes (for 3" diameter heater)
- Oxidation resistant
- Geometrically compatible with current reactor

- Disadvantages

- Maximum rated temperature of 950°C
- High cost: \$3,500 - \$3,800 for 3" diameter heater



Optical Heating Methods Tend to Be Esoteric and Complex

- No information found on companies who manufacture focused UV or IR radiation heaters was found
- In one RTCVD (rapid thermal) setup, tungsten coil lamps are used in conjunction with mirrors lining the chamber to focus stray light on the substrate
- fast heating applications
 - requires fairly high angle of incidence to avoid requiring mirrors to maintain reasonable efficiency